

Supplementary Material

**Stacking Effects in van der Waals Heterostructures of BlueP and
Janus XYO (X=Ti, Zr, Hf; Y=S, Se) monolayers**

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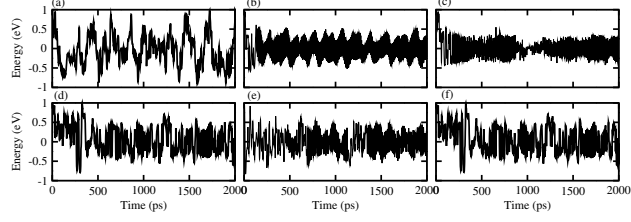


Fig.S 1: Thermal stabilities of strained (a) TiSO, (b) TiSeO, (c) ZrSO, (d) ZrSeO, (e) HfSO, and (f) HfSeO,

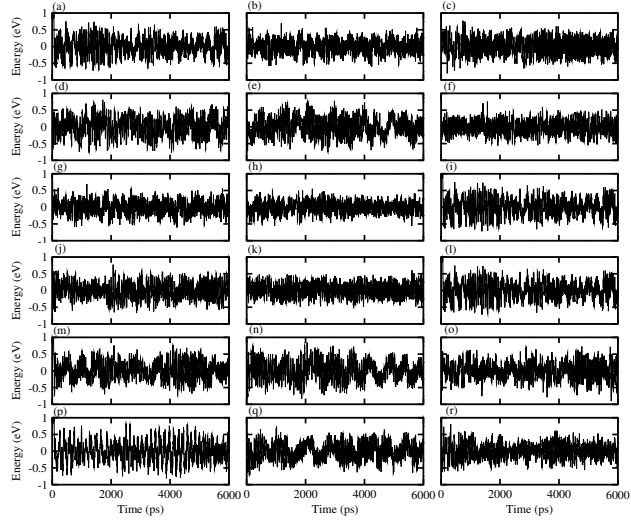


Fig.S 2: Thermal stabilities of blueP-TiSO ((a)-(c)), blueP-TiSeO ((d)-(f)), blueP-ZrSO ((g)-(i)), blueP-ZrSeO ((j)-(l)), blueP-HfSO ((m)-(o)), and blueP-HfSeO ((p)-(r)), where first column is for stacking-I, second column is for stacking-II and third column is for stacking-III of the corresponding vdW heterostructures

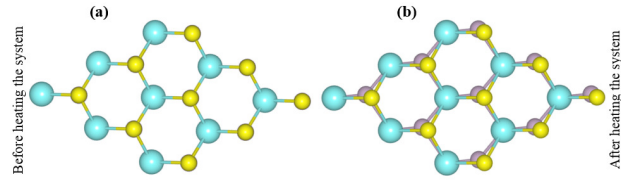


Fig.S 3: The atomic structure of the TiSeO monolayer (a) before and (b) after heating 6 ps, with no structure distortion.

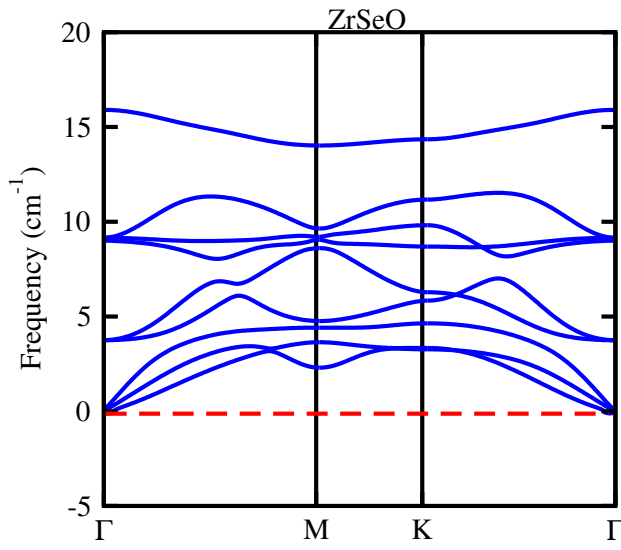


Fig.S 4: Phonon spectrum for 10% tensile strained ZrSSe.

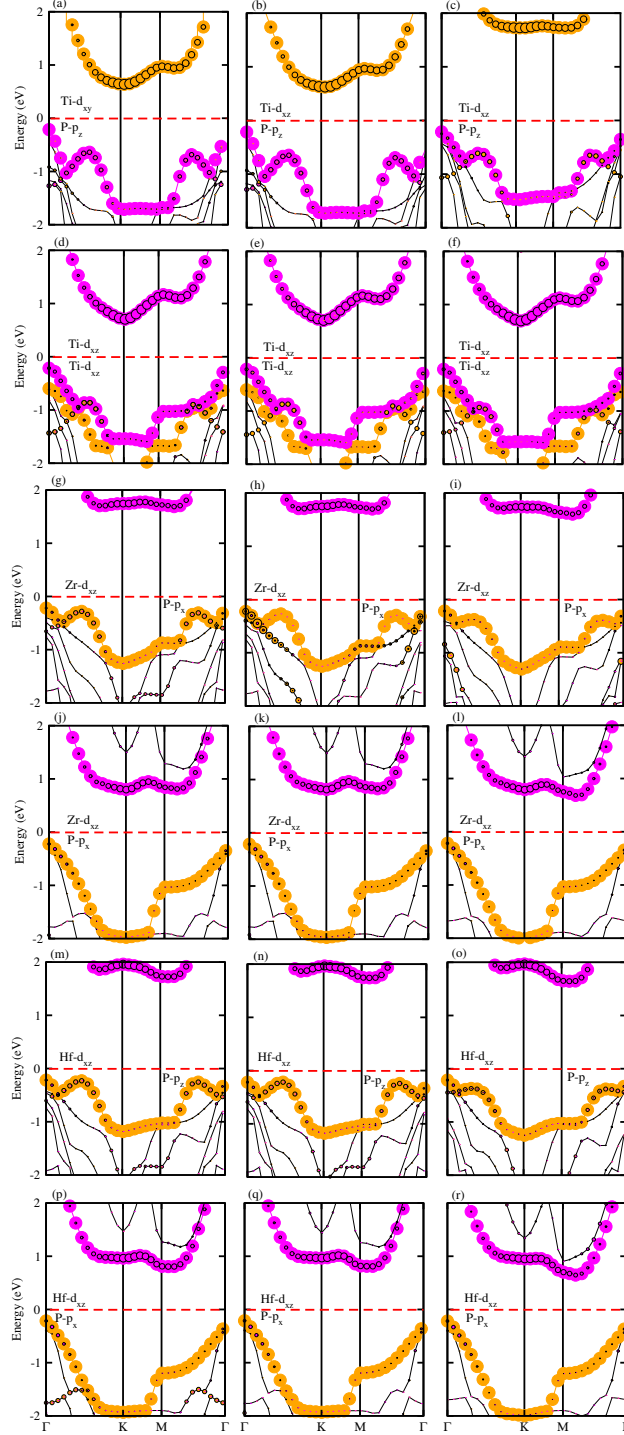


Fig.S 5: Weighted band structure of blueP-TiSO ((a)-(c)), blueP-TiSeO ((d)-(f)), blueP-ZrSO ((g)-(i)), blueP-ZrSeO ((j)-(l)), blueP-HfSO ((m)-(o)), and blueP-HfSeO ((p)-(r)), where first column is for stacking-I, second column is for stacking-II and third column is for stacking-III of the corresponding vdW heterostructures

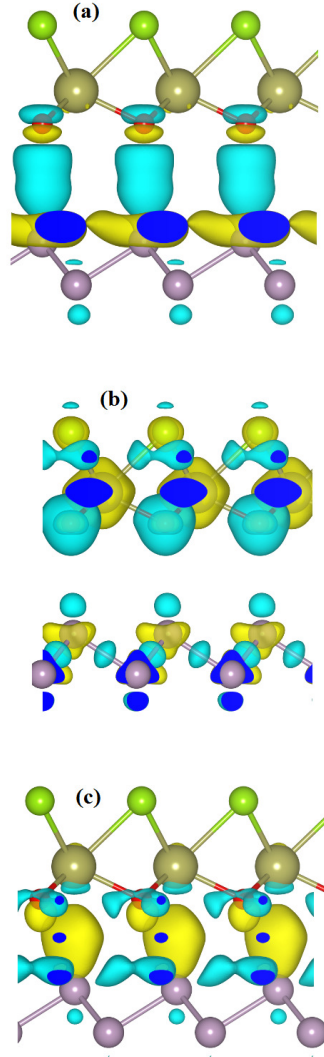


Fig.S 6: Charge density difference of the blueP-TiSO vdW heterostructure (for all three stackings), where the isovalue chosen to plot the isosurface is $0.001 \text{ eV \AA}^{-3}$

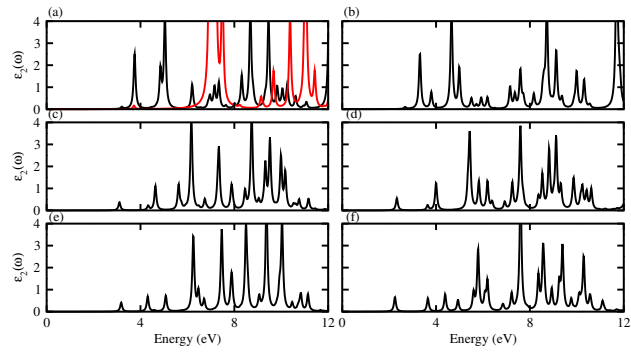


Fig.S 7: Imaginary part of dielectric function of (a) TiSO, (b) TiSeO, (c) ZrSO, (d) ZrSeO, (e) HfSO, and (f) HfSeO

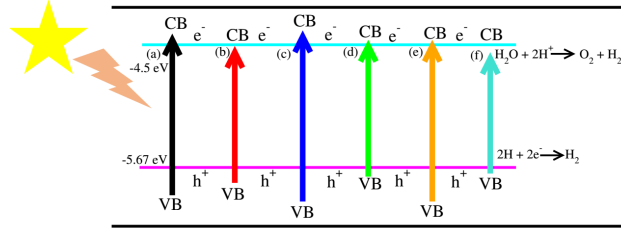


Fig.S 8: Valence band (E_{VB}) and conduction band (E_{CB}) edge alignment of (a) TiSO, (b) TiSeO, (c) ZrSO, (d) ZrSeO, (e) HfSO, and (f) HfSeO. The standard oxidation (-5.67 eV) and reduction (-4.44 eV) potentials for water splitting into $O_2 = H_2O$ and $H^+ = H_2$, respectively